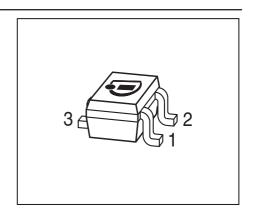


Low Noise Silicon Bipolar RF Transistor

- For low noise, high-gain broadband amplifiers at collector currents from 1 mA to 20 mA
- f_T = 8 GHz, NF_{min} = 0.9 dB at 900 MHz
- Pb-free (RoHS compliant) and halogen-free package with visible leads
- Qualification report according to AEC-Q101 available







ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pir	Configura	tion	Package
BFR182W	RGs	1=B	2=E	3=C	SOT323

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	12	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	2	
Collector current	I _C	35	mA
Base current	I _B	4	
Total power dissipation ¹⁾	P _{tot}	250	mW
<i>T</i> _S ≤ 90 °C			
Junction temperature	T _J	150	°C
Ambient temperature	T _A	-65 150	
Storage temperature	T_{Stq}	-65 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	240	K/W

1

 $^{{}^{1}}T_{\rm S}$ is measured on the collector lead at the soldering point to the pcb

 $^{^2}$ For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit	
		min.	typ.	max.		
DC Characteristics						
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	12	-	-	V	
$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$						
Collector-emitter cutoff current	I _{CES}				nA	
$V_{CE} = 4 \text{ V}, V_{BE} = 0$		-	1	30		
V_{CE} = 15 V, V_{BE} = 0 V, T_{A} = 85 °C		-	5	70		
(verified by random sampling)						
Collector-base cutoff current	I _{CBO}	-	1	30		
$V_{CB} = 4 \text{ V}, I_{E} = 0$						
Emitter-base cutoff current	I _{EBO}	-	-	50		
$V_{EB} = 1 \text{ V}, I_{C} = 0$						
DC current gain	h _{FE}	70	100	140	-	
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, pulse measured						



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling	g)		1	1	
Transition frequency	f_{T}	6	8	-	GHz
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, f = 500 MHz					
Collector-base capacitance	C _{cb}	-	0.34	0.5	pF
$V_{\text{CB}} = 10 \text{ V}, f = 1 \text{ MHz}, V_{\text{BE}} = 0$,					
emitter grounded					
Collector emitter capacitance	C _{ce}	-	0.26	-	
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,					
base grounded					
Emitter-base capacitance	C _{eb}	-	0.8	-	
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$,					
collector grounded					
Minimum noise figure	<i>NF</i> _{min}				dB
$I_{\rm C}$ = 3 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,					
f = 900 MHz		-	0.9	-	
$I_{\rm C}$ = 3 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,					
f = 1.8 GHz		-	1.3	-	
Power gain, maximum stable ¹⁾	G _{ms}	-	19	-	dB
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 900 MHz					
Power gain, maximum available ²⁾	G _{ma}	-	12.5	_	dB
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 1.8 GHz					
Transducer gain	S _{21e} ²				dB
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 900 MHz		-	15.5	_	
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 1.8 GHz		_	10	_	

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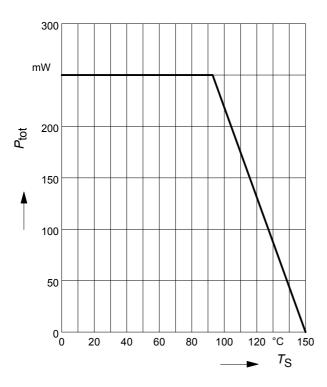
 $^{{}^{1}}G_{ms} = |S_{21} / S_{12}|$

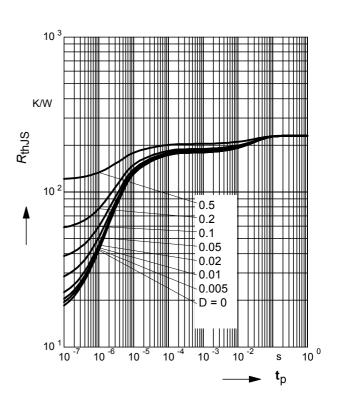
 $^{{}^{2}}G_{\text{ma}} = |S_{21e} / S_{12e}| (k-(k^{2}-1)^{1/2})$



Total power dissipation $P_{\text{tot}} = f(T_{\text{S}})$

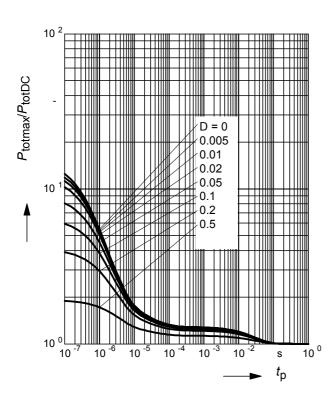
Permissible Pulse Load $R_{thJS} = f(t_p)$





Permissible Pulse Load

$$P_{\text{totmax}}/P_{\text{totDC}} = f(t_{p})$$

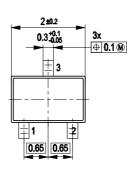


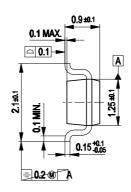
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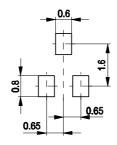
Package Outline



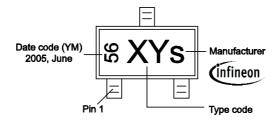




Foot Print

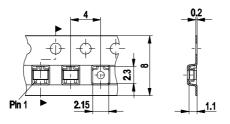


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel





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